

2SK2573(Tentative)

Silicon N-Channel Power F-MOS

■ Features

- Avalanche energy capability guaranteed
- High-speed switching
- Low ON-resistance
- No secondary breakdown

■ Applications

- Non-contact relay
- Solenoid drive
- Motor drive
- Control equipment
- Switching mode regulator

■ Absolute Maximum Ratings (T_c = 25°C)

Parameter		Symbol	Rating	Unit
Drain-Source breakdown voltage		V _{DSS}	500	V
Gate-Source voltage		V _{GSS}	±30	V
Drain current	DC	I _D	±20	A
	Pulse	I _{DP}	±40	A
Avalanche energy capability		EAS *	20	mJ
Allowable power dissipation	T _C = 25°C	P _D	100	W
	Ta= 25°C		3	
Channel temperature		T _{ch}	150	°C
Storage temperature		T _{stg}	−55 to +150	°C

* L = 0.1mH, I_L = 20A, 1 pulse

■ Electrical Characteristics (T_c = 25°C)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source cut-off current	I _{DSS}	V _{DS} = 400V, V _{GS} = 0			100	μA
Gate-Source leakage current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0			±1	μA
Drain-Source breakdown voltage	V _{DSS}	I _D = 1mA, V _{GS} = 0	500			V
Gate threshold voltage	V _{th}	V _{DS} = 25V, I _D = 1mA	1		5	V
Drain-Source ON-resistance	R _{DS(on)}	V _{GS} = 10V, I _D = 10A		0.32	0.4	Ω
Forward transadmittance	Y _{fs}	V _{DS} = 25V, I _D = 10A	7.2	12		S
Diode forward voltage	V _{DSF}	I _{DR} = 20A, V _{GS} = 0			-2.8	V
Input capacitance	C _{iss}	V _{DS} = 20V, V _{GS} = 0, f = 1MHz		3000		pF
Output capacitance	C _{oss}			430		pF
Feedback capacitance	C _{rss}			175		pF
Turn-on time	t _{on}	V _{DD} = 150V, I _D = 10A V _{GS} = 10V, R _L = 15Ω		150		ns
Fall time	t _f			140		ns
Turn-off time (delay time)	t _{d(off)}			480		ns
Channel-Case heat resistance	R _{th(ch-c)}				1.25	°C/W
Channel-Atmosphere heat resistance	R _{th(ch-a)}				41.67	°C/W

